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(71) Applicants (for all designated States except US): SAM-SUNG ELECTRONICS CO., LTD. [KR/KR]; 416, Mae-tan-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do 442-742 (KR). NATIONAL INSTITUTE OF ADVANCED INDUSTRIAL SCIENCE AND TECHNOLOGY [JP/JP]; 1-3-1, Kasumigaseki, Chiyoda-ku, Tokyo 100-8921 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): KIM, Joo-Ho

[KR/KR]; 104-901 SK Apt., 700, Seocheon-ri, Gi-heung-eup, Yongin-si, 449-900 Gyeonggi-do (KR). TOMINAGA, Junji [JP/JP]; 111, Higashi, Tsukubasi, Ibaraki 305-8562 (JP).

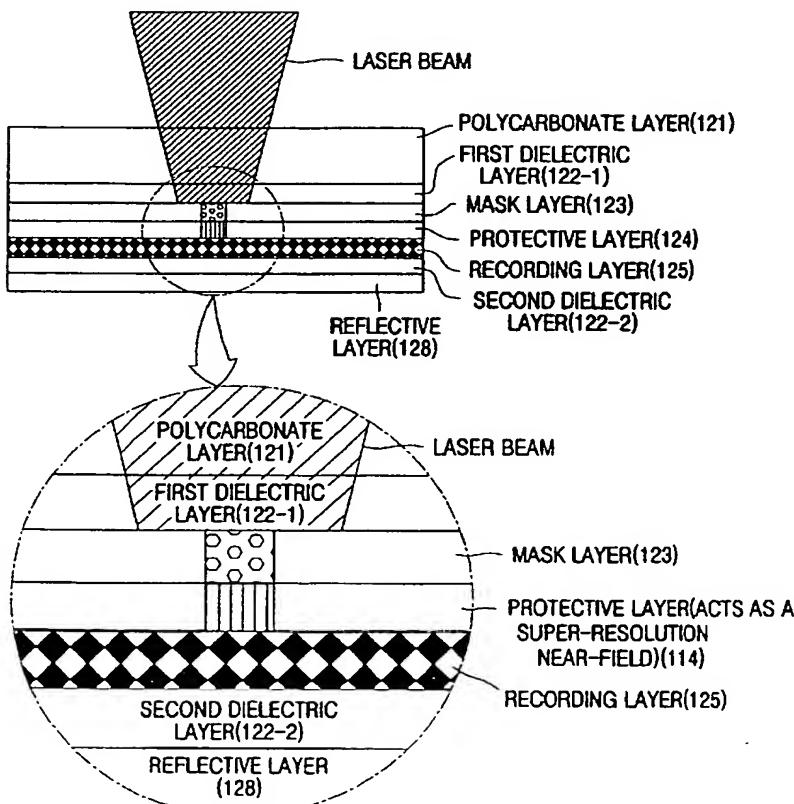
(74) Agent: LEE, Young-Pil; The Cheonghwa Building, 1571-18, Seocho-dong, Seocho-gu, 137-874 Seoul (KR).

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(54) Title: HIGH DENSITY RECORDING MEDIUM WITH SUPER-RESOLUTION NEAR-FIELD STRUCTURE MANUFACTURED USING HIGH-MELTING POINT METAL OXIDE OR SILICON OXIDE MASK LAYER



(57) Abstract: A high density recording medium with a super-resolution near-field structure including a mask layer comprising high melting point metal oxide or silicon oxide is provided. More particularly, A high density recording medium with a super-resolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer comprises high melting point metal oxide or silicon oxide to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the high melting point metal oxide or silicon oxide is provided.

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